GUFB30M

SINTERED GLASS JUNCTION PLASTIC RECTIFIER

VOLTAGE: 1000V CURRENT: 3.0A



FEATURE

High temperature metallurgically bonded construction Sintered glass cavity free junction Capability of meeting environmental standard of MIL-S-19500 High temperature soldering guaranteed 350°C /10sec/0.375"lead length at 5 lbs tension Operate at Ta =55°C with no thermal run away Typical Ir<0.1 μ A

MECHANICAL DATA

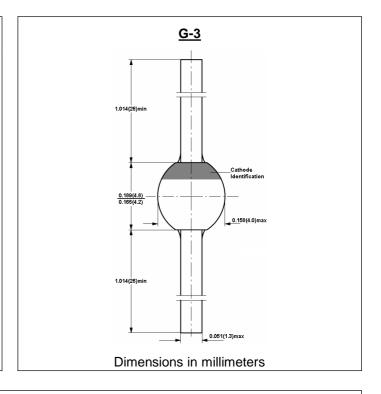
Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C

Case: Molded with UL-94 Class V-0 recognized Flame

Retardant Epoxy

Polarity: color band denotes cathode

Mounting position: any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

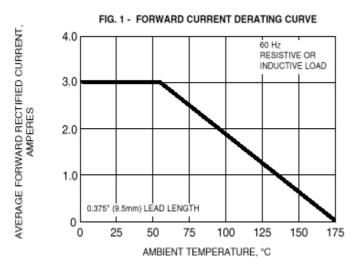
		SYMBOL	GUFB30M	units
Maximum Recurrent Peak Reverse Voltage		Vrrm	1000	V
Maximum RMS Voltage		Vrms	700	V
Maximum DC blocking Voltage		Vdc	1000	V
Maximum Average Forward Rectified Current 3/8"lead length at Ta =55°C		If(av)	3.0	А
Peak Forward Surge Current 8.3ms single Half sinewave superimposed on rated load		Ifsm	80.0	А
Maximum Instantaneous Forward Voltage at 9.0A		Vf	1.70	V
Maximum DC Reverse Current at rated DC blocking voltage	Ta =25°C Ta =150°C	lr	10.0 100.0	μА
Maximuml Reverse Recovery Time	(Note 1)	Trr	75	nS
Typical Junction Capacitance	(Note 2)	Cj	40.0	pF
Typical Thermal Resistance	(Note 3)	Rth(ja)	20.0	°C /W
Storage and Operating Junction Temperature		Tstg, Tj	-65 to +175	°C

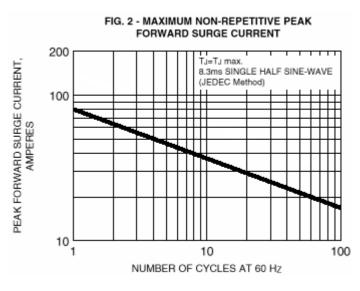
Note:

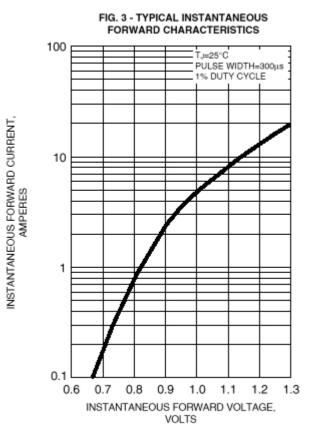
- 1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 3. Thermal Resistance from Junction to Ambient at 3/8"lead length, P.C. Board Mounted

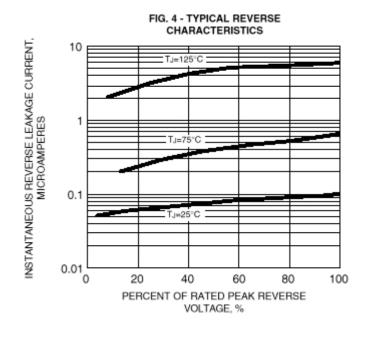
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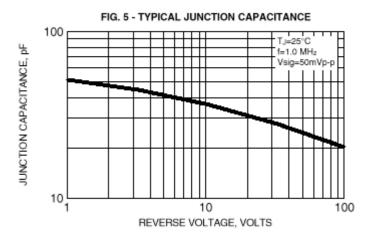
RATINGS AND CHARACTERISTIC CURVES GUFB30M











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